

SILICON TRANSISTOR 2SD1583-Z

NPN SILICON EPITAXIAL TRANSISTOR MP-3

DESCRIPTION

2SD1583-Z is designed for Audio Frequency Amplifier and Switching, especially in Hybrid Integrated Circuits.

FEATURES

- High hre: hre= 800 to 3 200
- Low VCE(sat) VCE(sat) = 0.18 V TYP.

QUALITY GRADE

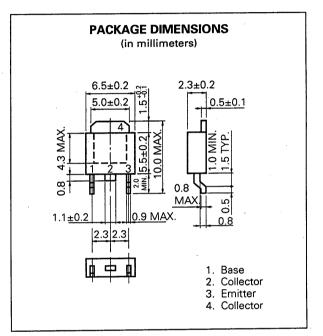
Standard

Please refer to "Quality grade on NEC Semiconductor Devices" (Document number IEI-1209) published by NEC Corporation to know the specification of quality grade on the devices and its recommended applications.

ABSOLUTE MAXIMUM RATINGS (Ta = 25 °C)

Collector to Base Voltage	Vсво	30	٧
Collector to Emitter Voltage	Vceo	20	٧
Emitter to Base Voltage	Vево	5	٧
Collector Current (DC)	lc	2	Α
Collector Current (Pulse)*	lc	' 3	Α
Total Power Dissipation (Ta = 25 °C)**	Рт	2.0	W
Junction Temperature	T_{j}	150	°C
Storage Temperature	Tstg	-55 to +150	°C

- * PW ≦ 10 ms, Duty Cycle ≦ 50 %
- ** When mounted on ceramic substrate of 7.5 cm² x 0.7 mm



ELECTRICAL CHARACTERISTICS (Ta = 25 °C)

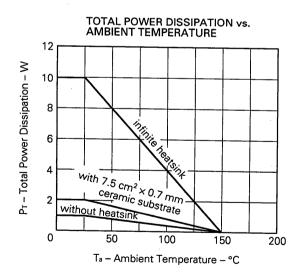
CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
Collector Cutoff Current	Ісво			10	μΑ	VcB = 20 V, IE = 0
Emitter Cutoff Current	IEBO.			10	μΑ	VEB = 5.0 V, IC = 0
DC Current Gain	hFE1*	600	2 000			VcE = 5.0 V, lc = 50 mA
DC Current Gain	hFE2*	800	2 000	3 200		VCE = 5.0 V, Ic = 0.5 A
DC Current Gain	hFE3*	500	1 400			VCE = 5.0 V, Ic = 2.0 A
Collector Saturation Voltage	VCE(sat)*		0.18	0.5	V	lc = 1.0 A, lB = 10 mA
Base Saturation Voltage	VBE(sat)*		0.85	1.2	V	Ic = 1.0 A, IB = 10 mA
Gain Bandwidth Product	fr		270		MHz	Vce = 5.0 V, le = 100 mA
Output Capacitance	Соь		20		pF	VcB = 10 V, IE = 0, f = 1.0 MHz
Turn-on Time	ton		0.6		μs	
Storage Time	tstg		1.5		μs	lc = 1A,Vcc ≒ 10 V
Fall Time	tf		0.3		μs	l _{B1} = -l _{B2} = 10 mA

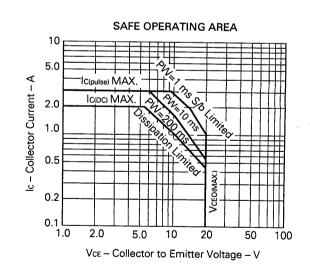
^{*} Pulsed: PW \leq 350 μ s, Duty Cycle \leq 2 %

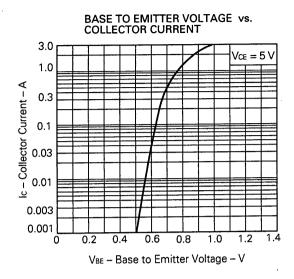
hre Classification

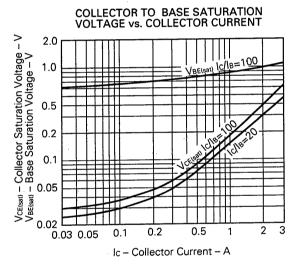
MARKING	М	L	К
hFE2	800 to 1 600	1 000 to 2 000	1 600 to 3 200

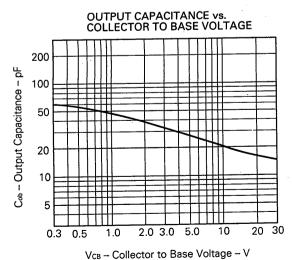
TYPICAL CHARACTERISTICS (Ta = 25 °C)

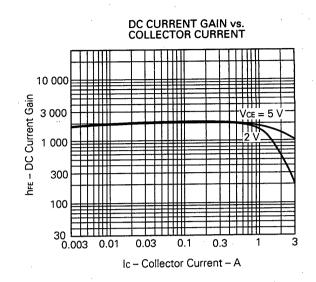


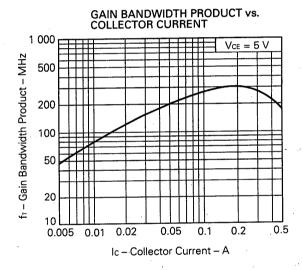












Reference

Application note name	No.
Quality control of NEC semiconductors devices.	TEI-1202
Quality control guide of semiconductors devices.	MEI-1202
Assembly manual of semiconductors devices.	IEI-1207
Design of Push-Pull Type Switching Regulators (Basic)	TEB-1002
Design of Push-Pull Type Switching Regulators (Applications)	TEB-1003
Optimum Base Drive Conditions of Switching Power Transistors	TEB-1014

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Application examples recommended by NEC Corporation.

Standard: Computer, Office equipment, Communication equipment, Test and Measurement equipment, Machine tools, Industrial robots, Audio and Visual equipment, Other consumer products, etc.

Special: Automotive and Transportation equipment, Traffic control systems, Antidisaster systems, Anticrime systems, etc.

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